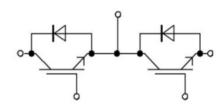


C1 series package: 1700V 150A IGBT module

Datasheet





Equivalent Circuit Schematic

Features:

- Trenchgate Gen.7 IGBT technology
- VCE(sat) with positive temperature coefficient
- High RBSOA capability
- Low static losses: VCE(sat) = 1,6V@25C
- Low dynamic losses

Options:

Pre-applied TIM (option +M01)

Typical Applications:

- Motor Drives
- Uninterrupted Power Suppl
- Photovoltaic



IGBT, Inverter / IGBT Maximum Rated Values

Collector-emitter Voltage	Tvj = 25°C	VCES	1700	V
Continuous DC Collector Current		ICnom	150	А
	Tc = 100°C, T _{vj max} = 175°C	Ic	180	Α
Repetitive Peak Collector Current	ICRM = 2 x Icnom	ICRM	300	Α
Total power dissipation	Tc = 25°C, T _{vj max} = 175°C	Ptot	830	А
Gate-emitter Peak Voltage		VGES	±20	V

Characteristic Values				min.	typ.	max.	
Collector-emitter Saturation Voltage ¹⁾	Ic = 150A, VgE = 15V	$Tv_j = 25^{\circ}C$ $Tv_j = 125^{\circ}C$ $Tv_j = 150^{\circ}C$ $Tv_j = 175^{\circ}C$	VCEsat		1.60 1.73 1.77 1.82		٧
Gate Threshold Voltage	VCE = VGE, IC = 3mA, Tvj = 25°C	;	VGEth	5.50	6.10	6.70	V
Gate Charge	VgE = -8V/15V, VcE = 900V, Tvj	= 25°C	QG	_	1.33	-	μC
Internal Gate Resistor	Tvj = 25°C		RGint	_	1.6	-	Ω
Input Capacitance	Vce = 25V, Vge = 0V		Cies	-	34.2	-	nF
Reverse Transfer Capacitance	f = 100kHz, T _{vj} = 25°C		Cres	-	0.10	_	nF
Collector-emitter Cutoff Current	VCE = 1700V, VGE = 0V, Tvj = 2	5°C	ICES	_	_	1	μA
Gate-emitter Leakage Current	VcE = 0V, VGE =20V, Tvj = 25°C	:	IGES	_	_	200	nA
Turn-on Delay Time, Inductive Load	IC = 150A, VCE = 900V VGE = ±15V Rgon = 4Ω	T _{vj} = 25°C T _{vj} = 125°C T _{vj} = 150°C T _{vj} = 175°C	tdon	-	125 125 130 135	-	ns
Rise Time, Inductive Load	Ic = 150A, VcE = 900V VGE = ±15V Rgon = 4.0Ω	$T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	tr	-	45 55 55 60	-	ns
Turn-off Delay Time, Inductive Load	IC = 150A, VCE = 900V VGE = \pm 15V RGoff = 4.0Ω	$T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	tdoff	-	370 430 445 460	-	ns
Fall Time, Inductive Load	IC = 150A, VCE = 900V VGE = \pm 15V RGoff = 4.0Ω	$T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	tf	-	295 585 680 780	-	ns
Turn-on Energy Loss per Pulse	IC = 150A, VCE = 900V, Lσ=28nH, VGE = ±15V, RGon = 4.0Ω, di/dt = 2000 A/μs (Tvj = 175°C)	T _{vj} = 25°C T _{vj} = 125°C T _{vj} = 150°C T _{vj} = 175°C	Eon	-	25.5 32.0 34.5 36.0	-	mJ
Turn-off energy Loss per Pulse	IC = 150A, VCE = 900V, $L\sigma$ =28nH, VGE = ±15V, R_{goff} = 4.0 Ω dv/dt = 3900 V/ μ s (Tv $_{j}$ = 175 $^{\circ}$ C)	T _{vj} = 25°C T _{vj} = 125°C T _{vj} = 150°C T _{vj} = 175°C	Eoff	_	26.0 45.0 50.0 55.0	_	mJ

¹⁾ Terminal impedance is not included.



SC Data	VcE = 1000 V	t _p ≤ 8us, T _{vj} = 150°C	Isc	680			А
	V _{GE} = ±15 V t _p ≤ 6us, T _{vj} = 175°C			650			
Thermal Resistance, Junction to Case	Per IGBT		RthJC	I	0.180	ı	K/W
Temperature under Switching Conditions ²⁾			Tvj op	-40		175	°C

Diode, Inverter Maximum Rated Values

Repetitive Peak Reverse Voltage	T _{vj} = 25°C	VRRM	1700	V
Continuous DC Forward Current		lF	150	Α
Repetitive Peak Forward Current	ICRM = 2 x Ifnom	IFRM	300	A

Characteristic Values				min.	typ.	max.	
Forward Voltage ¹⁾	IF = 150A, VGE = 0V	$T_{vj} = 25^{\circ}C$ $T_{vj} = 125^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	VF		1.57 1.67 1.67 1.66	2.40	V
Peak Reverse Recovery Current	IF = 150A, VR = 900V -di _F /dt = 3700A/us (T _{Vj} = 175°C) VGE = -15V	$Tv_j = 25^{\circ}C$ $Tv_j = 125^{\circ}C$ $Tv_j = 150^{\circ}C$ $Tv_j = 175^{\circ}C$	lгм	-	225 230 235 240	-	A
Recovery Charge	IF = 150A, VR = 900V -dir/dt = 3700A/us (Tvj = 175°C) VGE = -15V	$Tv_j = 25$ °C $Tv_j = 125$ °C $Tv_j = 150$ °C $Tv_j = 175$ °C	QR	ı	19.5 24.0 27.5 28.5	-	uC
Reverse Recovery Energy	IF = 150A, VR = 900V -di _F /dt = 3700A/us (T _{Vj} = 175°C) VGE = -15V	$Tv_j = 25^{\circ}C$ $Tv_j = 125^{\circ}C$ $Tv_j = 150^{\circ}C$ $Tv_j = 175^{\circ}C$	Erec	-	9.10 16.0 17.0 17.5	-	mJ
Thermal Resistance, Junction to Case	Per Doide		RthJC	_	0.238	_	K/W
Temperature under Switching Conditions ²⁾			Tvj op	-40	-	175	°C

Module

Isolation Test Voltage	RMS, f = 50Hz, t = 1min	Visol	3.0	kV
Material of Module Baseplate			Cu	
Internal Isolation	(class 1, IEC 61140) Basic insulation (class 1, IEC 61140)		AL2O3	
Creepage Distance	Terminal to heatsink Terminal to terminal		17.0 20.0	mm
Clearance	Terminal to heatsink Terminal to terminal		17.0 9.5	mm
Comparative Tracking Index		СТІ	>200	



min. typ. max.

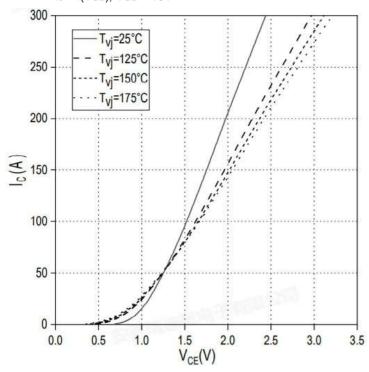
Thermal resistance, case to heatsink	per module λPaste = 1W/(m·K)/λgrease = 1W/(m·K)	RthCH		0.05		K/W
Stray Inductance Module		LsCE	-	30	-	nΗ
Module Lead Resistance, Terminals-Chip	Tc = 25°C, Per Switch	Rcc'+EE'	-	0.65	-	mΩ
Storage Temperature		Tstg	-40	_	125	°C
Modul MountingTorque	M6	М	4.0	_	6.0	Nm
Terminal MountingTorque	M5	М	3.0	_	6.0	Nm
Weight		G	-	145	-	g

¹⁾ Terminal impedance is not included. 2) $T_{Vj\ op} > 150^{\circ}C$ is only allowed for operation at overload conditions.

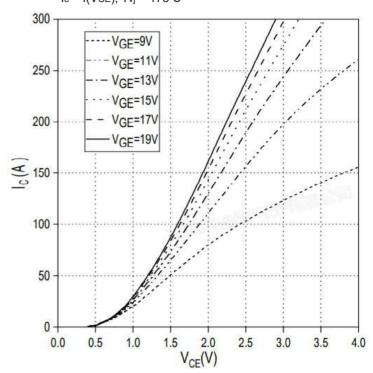


Circuit Diagram

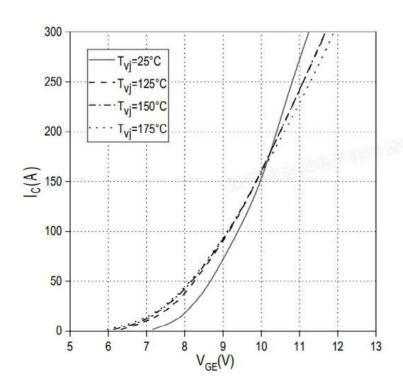
Output characteristic IGBT, Inverter (typical), IGBT Ic = f(VCE), VGE = 15V



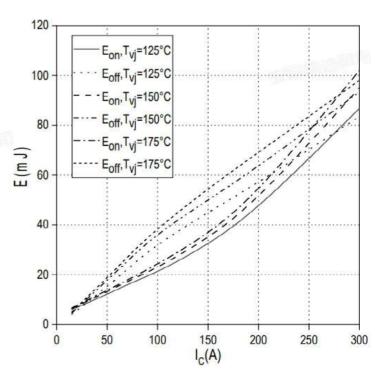
Output characteristic IGBT, Inverter (typical), IGBT $I_C = f(VCE)$, $T_{Vj} = 175$ °C



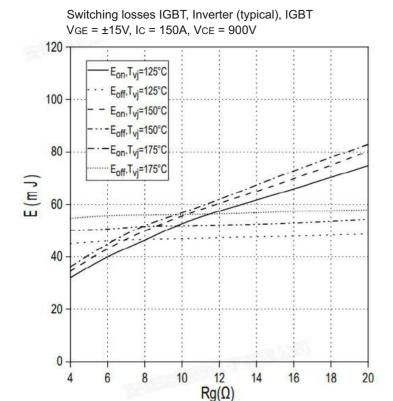
Transfer characteristic IGBT,Inverter(typical), IGBT $I_c = f(VGE)$, VCE = 20V

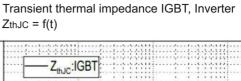


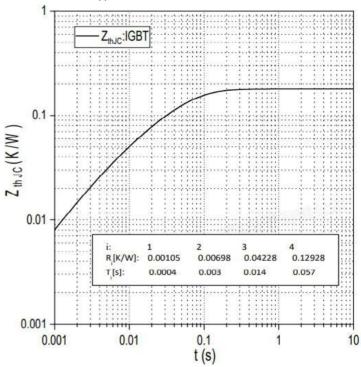
Switching losses IGBT, Inverter (Typical), IGBT Eon = f(Ic), Eoff = f(Ic) VGE = ± 15 V, RGon = 4Ω , RGoff = 4Ω , VCE = 900V



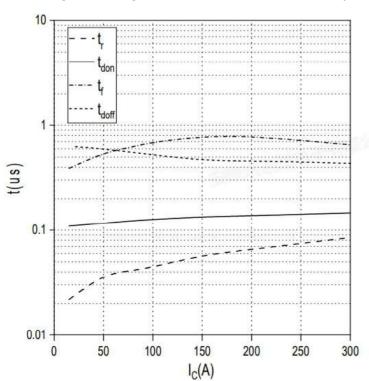




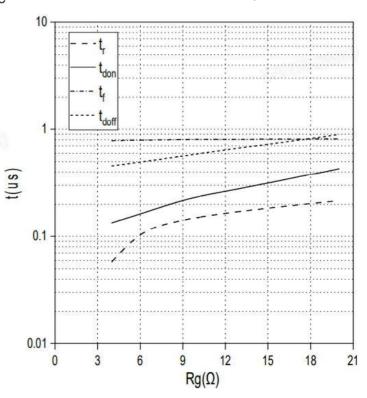




Switching time IGBT, Inverter (typical) $R_{goff} = 4.0\Omega$, $R_{gon} = 4.0\Omega$, VCE = 900V, $VGE = \pm 15V$, $T_{Vj} = 175^{\circ}C$

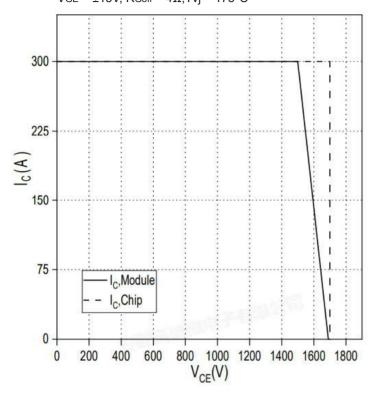


Switching time IGBT, Inverter (typical) t = f(Rg) $IC = 150A, VCE = 900V, VGE = \pm 15V, Tvj = 175°C$

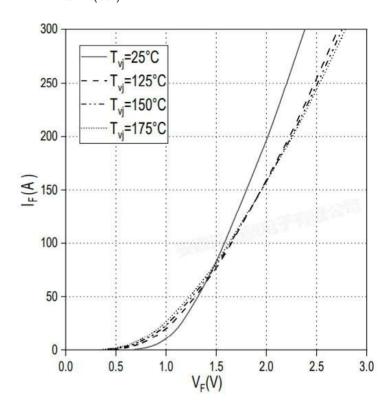




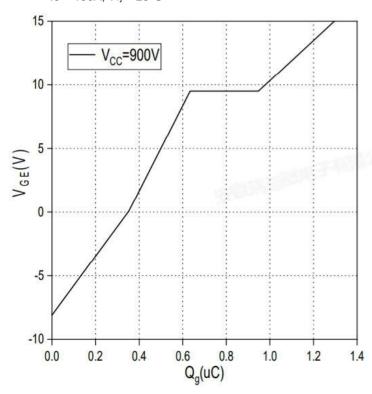
Reverse bias safe operating area IGBT, Inverter (RBSOA) Ic = f(VcE), VGE = ± 15 V, RGoff = 4Ω ,Tvj = 175°C



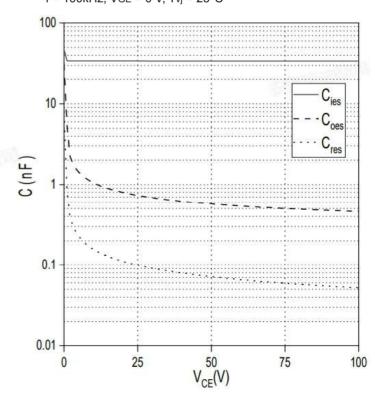
Forward characteristic of Diode, Inverter (typical) IF = f(VF)



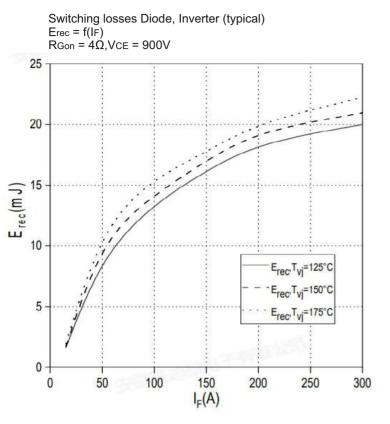
Gate charge characteristic, IGBT, Inverter (typical) VGE = f(Qg) Ic = 150A, Tvj = 25°C

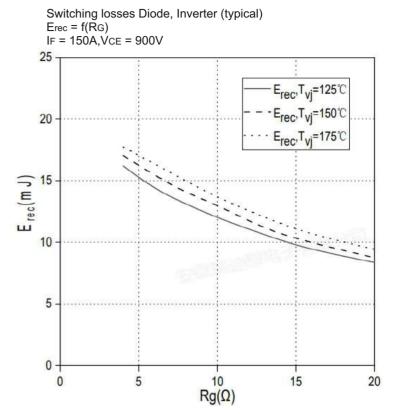


Capacity characteristic, IGBT, Inverter (typical) C = f(VCE) f = 100kHz, VGE = 0 V, Tvj = 25°C

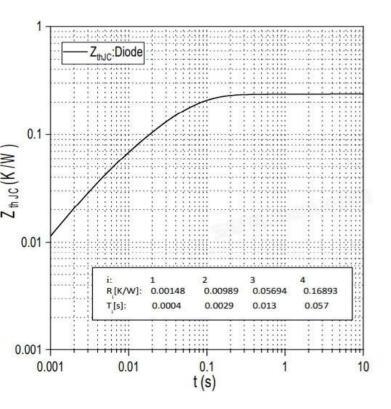






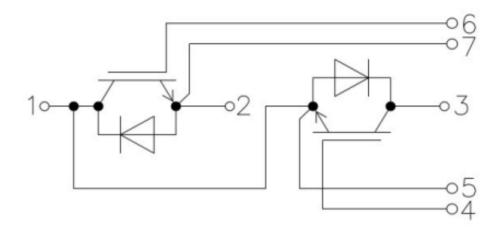


Transient thermal impedance Diode , Inverter $Z_{thJC} = f(t)$

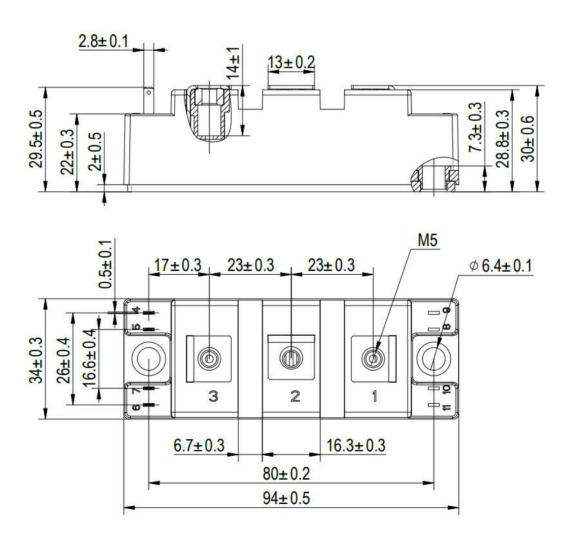




Internal Circuit



Package Dimension Dimensions in Millimeters



Rev.1 2025-11-28



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